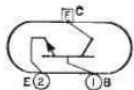


POWER TRANSISTOR



Silicon n-p-n type used in a wide variety of high-power applications in industrial and commercial equipment. This type is particularly useful in power-switching circuits in series and shunt-regulator driver

2N3055

and output stages, and in high-fidelity amplifiers. It is designed to assure freedom from second breakdown and features an exceptionally high dissipation rating. JEDEC No. TO-3 package; outline 5, Outlines Section.

MAXIMUM RATINGS

Collector-to-Base Voltage	100 max	volts
Collector-to-Emitter Voltage:		
With base open	60 max	volts
With external base-to-emitter resistance = 100 ohms	70 max	volts
With base-to-emitter volts = 1.5 volts	100 max	volts
Emitter-to-Base Voltage	7 max	volts
Collector Current	15 max	amperes
Base Current	7 max	amperes
Transistor Dissipation:		
At case temperatures up to 25°C	115 max	watts
At case temperatures above 25°C	See curve page 80	
Temperature Range:		
Operating and Storage	-65 to 200	°C
Lead Temperature (for 10 seconds maximum)	235 max	°C

CHARACTERISTICS

Collector-to-Emitter Sustaining Voltage:		
With external base-to-emitter resistance = 0 and collector ma = 200	60 min	volts
With external base-to-emitter resistance = 100 ohms and collector ma = 200	70 min	volts

Collector-to-Emitter Saturation Voltage (with collector amperes = 4 and base ma = 400)	1.1 max	volts
Base-to-Emitter Saturation Voltage (with collector-to-emitter volts = 4, and collector amperes = 4)	1.8 max	volts
Emitter-Cutoff Current (with emitter-to-base volts = 7 and collector current = 0)	5 max	ma
Thermal Resistance (junction-to-case)	1.5 max	°C/watt

In Common-Emitter Circuit

DC Forward Current-Transfer Ratio (with collector-to-emitter volts = 4 and collector amperes = 4)	20 to 70
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